

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK4096LS — General-Purpose Switching Device **Applications**

Features

- ON-resistance RDS(on)= 0.65Ω (typ.)
- · 10V drive

· Input capacitance Ciss=600pF

Specifications

Absolute Maximum Ratings at Ta=25°C

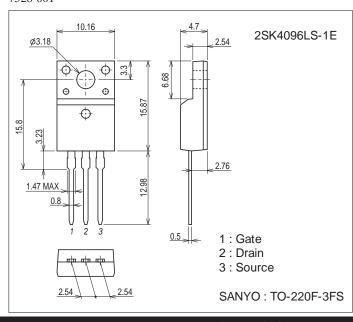
Parameter	Symbol	Conditions	Ratings	Unit	
Drain-to-Source Voltage	VDSS		500	V	
Gate-to-Source Voltage	VGSS		±30	V	
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	8	Α	
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	7.1	Α	
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	32	Α	
Allowable Power Dissipation	De		2.0	W	
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	33	W	
Channel Temperature	Tch		150	°C	
Storage Temperature	Tstg		-55 to +150	°C	
Avalanche Energy (Single Pulse) *4	EAS		354	mJ	
Avalanche Current *5	IAV		8	А	

Note:*1 Shows chip capability

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Package Dimensions

unit: mm (typ) 7528-001



Product & Package Information

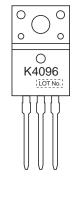
 Package : TO-220F-3FS

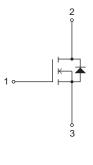
• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection





SANYO Semiconductor Co., Ltd.

http://www.sanyosemi.com/en/network/

^{*2} Package limited

^{*3} SANYO's condition is radiation from backside.

^{*4} VDD=50V, L=10mH, IAV=8A (Fig.1)

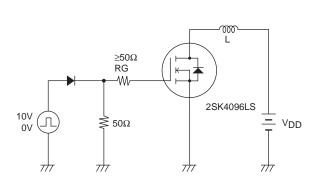
^{*5} L≤10mH, single pulse

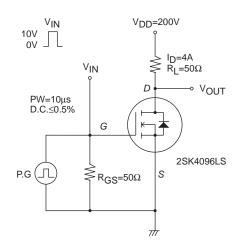
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Uill	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =400V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =4A	2.2	4.5		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =4A, V _G S=10V		0.65	0.85	Ω	
Input Capacitance	Ciss			600		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		130		pF	
Reverse Transfer Capacitance	Crss			28		pF	
Turn-ON Delay Time	t _d (on)			18.5		ns	
Rise Time	t _r	San Fig 2		46		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		75		ns	
Fall Time	tf			33		ns	
Total Gate Charge	Qg			24		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =8A		4.5		nC	
Gate-to-Drain "Miller" Charge	Qgd			14		nC	
Diode Forward Voltage	V _{SD}	I _S =8A, V _{GS} =0V		0.9	1.2	V	

Fig.1 Unclamped Inductive Switching Test Circuit

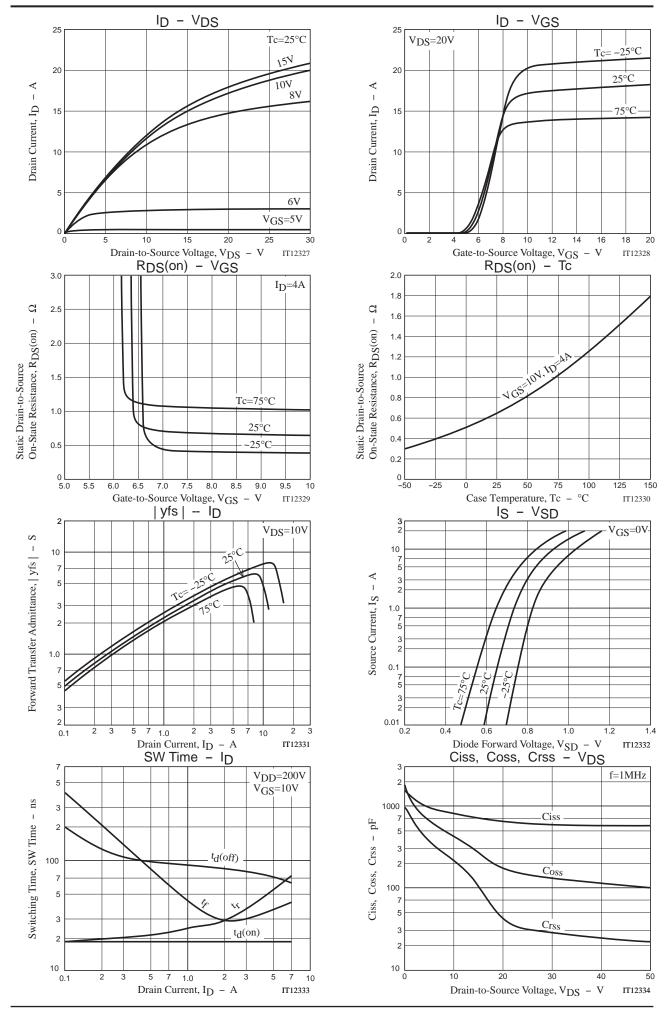
Fig.2 Switching Time Test Circuit

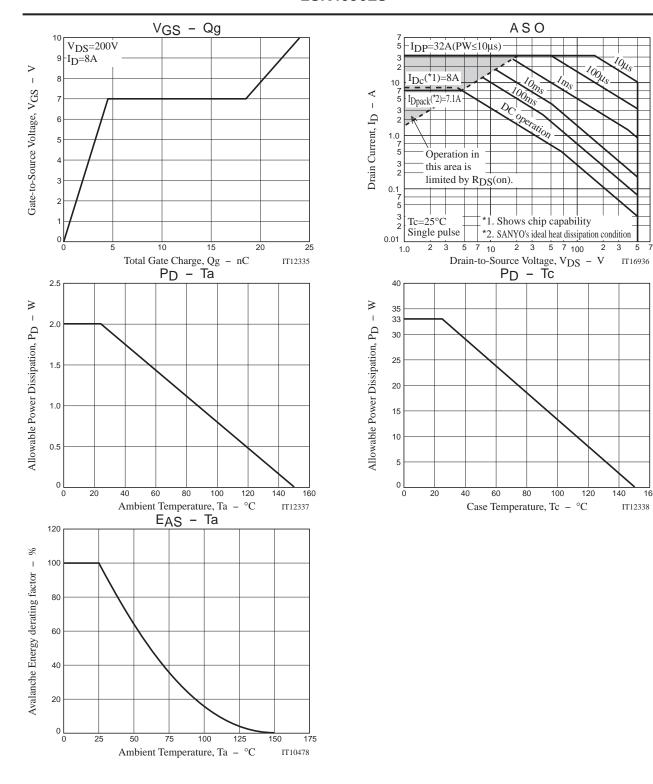




Ordering Information

Device	Package	Shipping	memo
2SK4096LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free





140

160

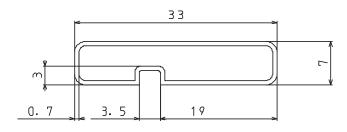
IT12338

Magazine Specification

2SK4096LS-1E

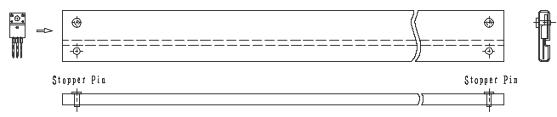
1. Packing Format

Package Name	Meximum Number of devices contained (pcs) Magazine Name Magazine Inver box Outer box		Packing format			
1 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4			Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178



Tolerance=±0, 3mm
Thickness=0, 7±0, 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

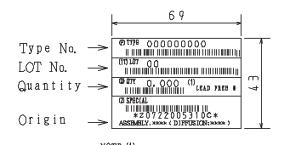
3. Storage method to magazine

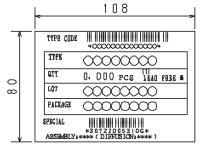


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



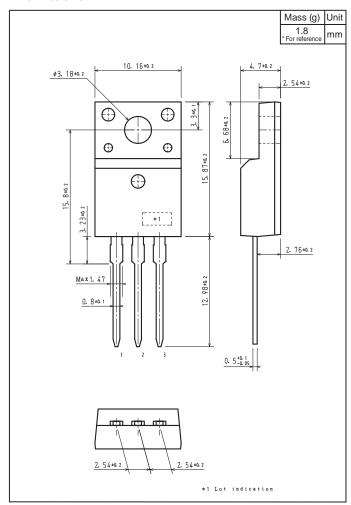


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK4096LS-1E



Note on usage: Since the 2SK4096LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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